

Sheet 1 of 1
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Application No.:
NEW NATIONAL PHASE

INFORMATION DISCLOSURE CITATION IN AN APPLICATION			Attorney Docket No.: 8017-1156		
(Use several sheets if necessary)			Applicant: Akira USUI et al.		
			Filing Date: December 30, 2004	Group Art Unit:	
U.S. PATENT DOCUMENTS					
Examiner Initial	Document Number	Date	Name	Class	Subclass
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FOREIGN PATENT DOCUMENTS					
Examiner Initial	Document Number	Date	Country	Class	Subclass
<i>EV</i>	1 271 627	1/2/2003	EUROPE		
<i>EV</i>	63-188983	8/4/1988	JAPAN		X
<i>EV</i>	10-312971	11/24/1998	JAPAN		X
<i>EV</i>	2000-012900	1/14/2000	JAPAN		X
<i>EV</i>	2001-223165	8/17/2001	JAPAN		X
<i>EV</i>	2001-284643	10/12/2001	JAPAN		X
<i>EV</i>	2002-050585	2/15/2002	JAPAN		X
<i>EV</i>	2002-050586	2/15/2002	JAPAN		X
<i>EV</i>	2002-343718	11/29/2002	JAPAN		X
<i>EV</i>	2003-178984	6/27/2003	JAPAN		X
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)					
<i>EV</i>	By Tsvetanka S. Zheleva et al., "Pendo-Epitaxy - A New Approach for Lateral Growth of Gallium Nitride Structures", MRS Internet J. Nitride Semicond. Res. 4S1, G3.38, 1999, pages 2-7.				
<i>EV</i>	By Ok-Hyun Nam et al., "Lateral Epitaxy of Low Defect Density GaN Layers Via Organometallic Vapor Phase Epitaxy", Appl. Phys. Lett., 71 (18), November 3, 1997, pages 1-4				
<i>EV</i>	By Masaru Kuramoto et al., "Room-Temperature Continuous-Wave Operation of InGaN Multi-Quantum-Well Laser Diodes Grown on an n-GaN Substrate with a Backside n-Contact", Japanese Journal of Applied Physics, Vol. 38, No. 2B, February 15, 1999, pages 1-4.				
<i>EV</i>	By Michael Kelly et al., "Large Free-Standing GaN Substrates by Hydride Vapor Phase Epitaxy and Laser-Induced Liftoff", Japanese Journal of Applied Physics, Vol. 38, No. 3A, March 1, 1999, pages 1-4.				
EXAMINER: <i>Glenn A. Leib</i>		DATE CONSIDERED <i>12/30/04</i>			
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